

Schnelle GaAs-IR-Lumineszenzdiode (950 nm) High-Speed GaAs Infrared Emitter (950 nm)

SFH 4200 SFH 4205



SFH 4200



SFH 4205

Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- Gleichstrom- (mit Modulation) oder Impulsbetrieb möglich
- Hohe Zuverlässigkeit
- Hohe Impulsbelastbarkeit
- Sehr kurze Schaltzeiten (10 ns)
- Für Oberflächenmontage geeignet
- Gegurtet lieferbar
- SFH 4200 Gehäusegleich mit SFH 320
- SFH 4205 Gehäusegleich mit SFH 325
- SFH 4205: Nur für IR-Reflow-Lötung geeignet.

Anwendungen

- Schnelle Datenübertragung mit Übertragungsraten bis 100 Mbaud (IR Tastatur, Joystick, Multimedia)
- Analoge und digitale Hi-Fi Audio- und Videosignalübertragung
- Batteriebetriebene Geräte (geringe Stromaufnahme)
- Anwendungen mit hohen Zuverlässigkeitsansprüchen bzw. erhöhten Anforderungen
- Alarm- und Sicherungssysteme
- IR Freiraumübertragung

Features

- Very highly efficient GaAs-LED
- DC (with modulation) or pulsed operations are possible
- High reliability
- High pulse handling capability
- Very short switching times (10 ns)
- Suitable for surface mounting (SMT)
- Available on tape and reel
- SFH 4200 same package as SFH 320
- SFH 4205 same package as SFH 325
- SFH 4205: Suitable only for IR-reflow soldering.

Applications

- High data transmission rate up to 100 Mbaud (IR keyboard, Joystick, Multimedia)
- Analog and digital Hi-Fi audio and video signal transmission
- Low power consumption (battery) equipment
- Suitable for professional and high-reliability applications
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 4200	Q62702-P978	Kathodenkennzeichnung: abgesetzte Ecke Cathode marking: bevelled edge TOPLED®
SFH 4205	Q62702-P5165	SIDELED

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	3	V
Durchlaßstrom Forward current	I_F (DC)	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	2.2	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm^2 Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm^2 each	R_{thJA}	450	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	200	K/W

Kennwerte ($T_A = 25\text{ °C}$)

Characteristics

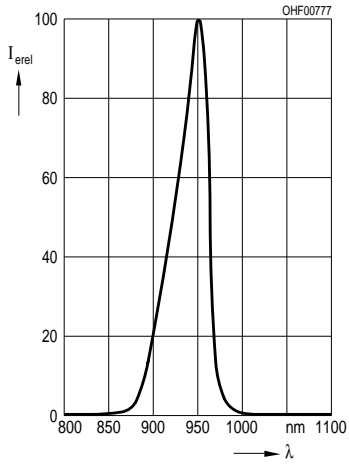
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$\Delta\lambda$	40	nm
Abstrahlwinkel Half angle	φ	± 60	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$, $R_L = 50\ \Omega$	t_r , t_f	10	ns
Durchlaßspannung, Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$	V_F V_F	1.5 (≤ 1.8) 3.2 (≤ 4.0)	V V
Sperrstrom, Reverse current $V_R = 3\text{ V}$	I_R	0.01 (≤ 10)	μA
Gesamtstrahlungsfluß, Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	28	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.44	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.2	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01$ sr**Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01$ sr

Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min.}}$ $I_{e \text{ typ.}}$	4 8.5	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	55	mW/sr

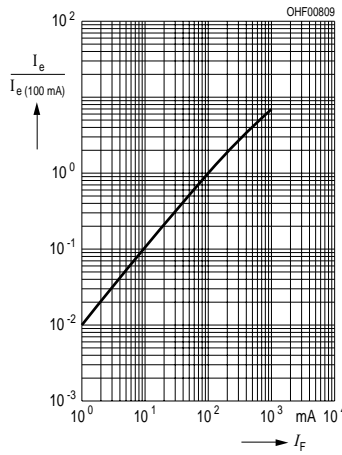
Relative Spectral Emission

$I_{rel} = f(\lambda)$



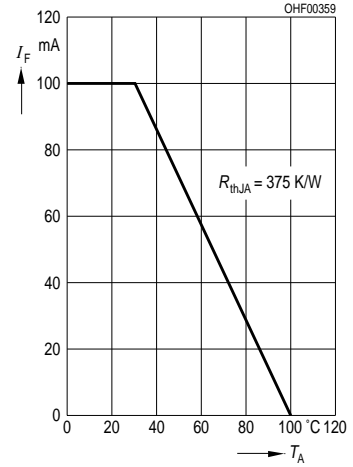
Radiant Intensity $\frac{I_e}{I_e(100\text{ mA})} = f(I_F)$

Single pulse, $t_p = 20\ \mu\text{s}$



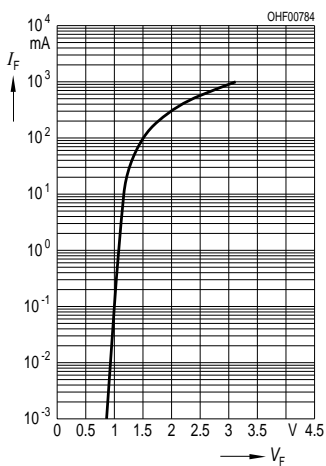
Max. Permissible Forward Current

$I_F = f(T_A)$



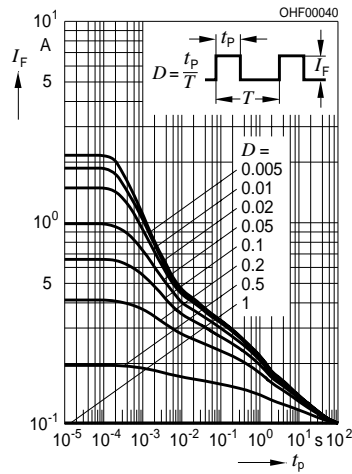
Forward Current $I_F = f(V_F)$

single pulse, $t_p = 20\ \mu\text{s}$

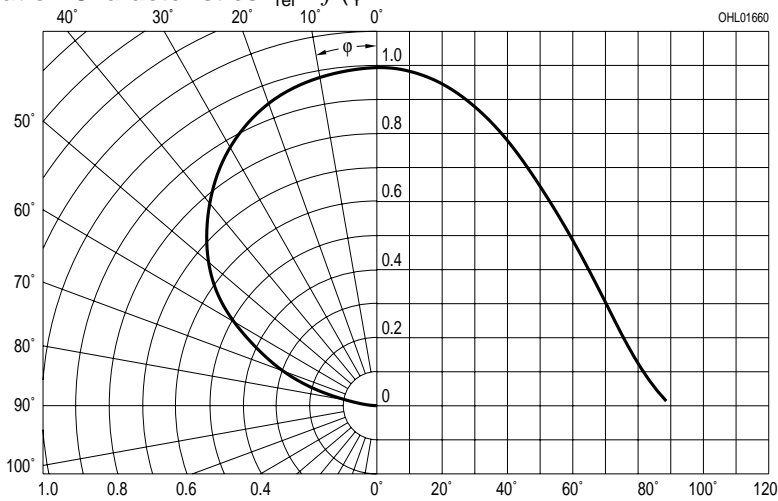


Permissible Pulse Handling Capability

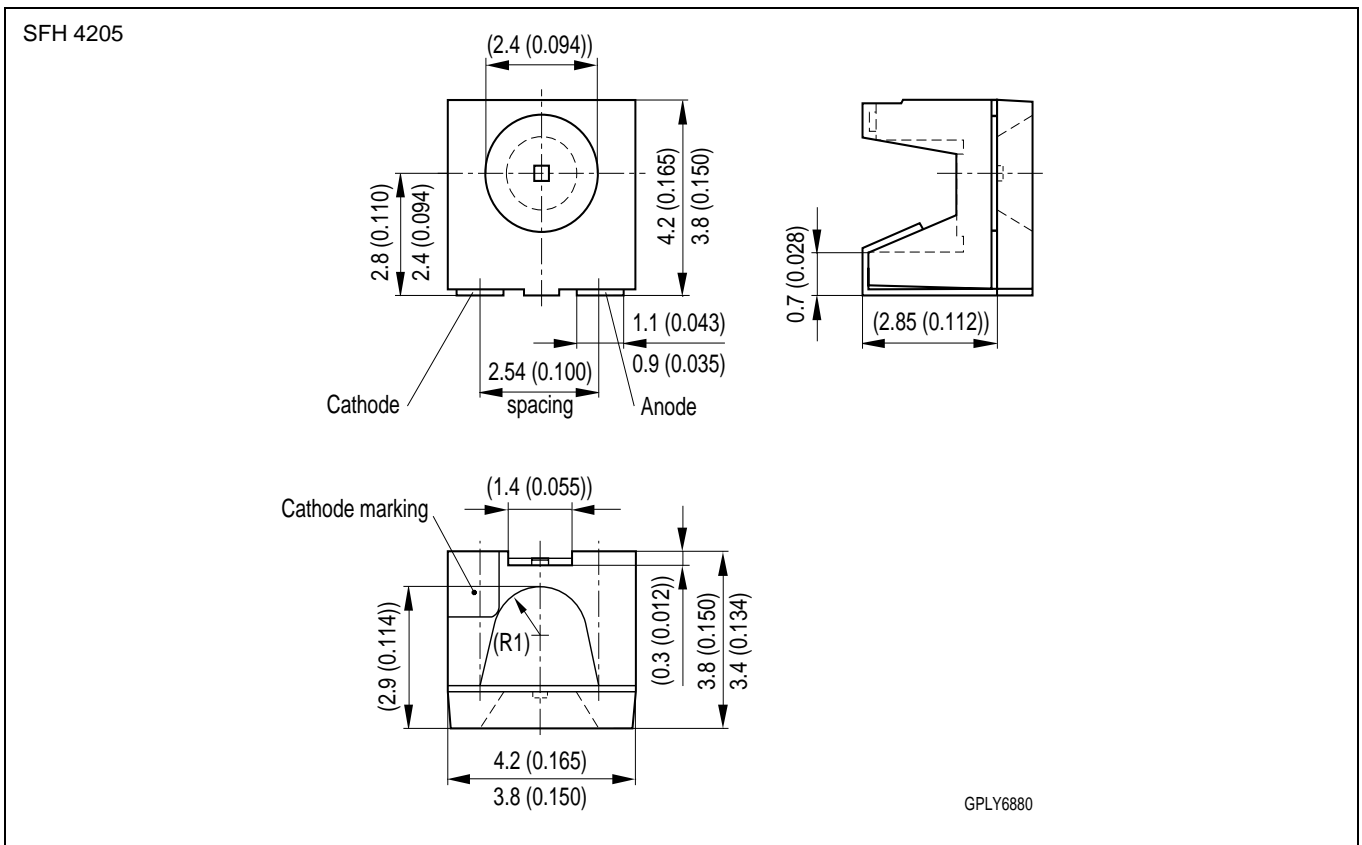
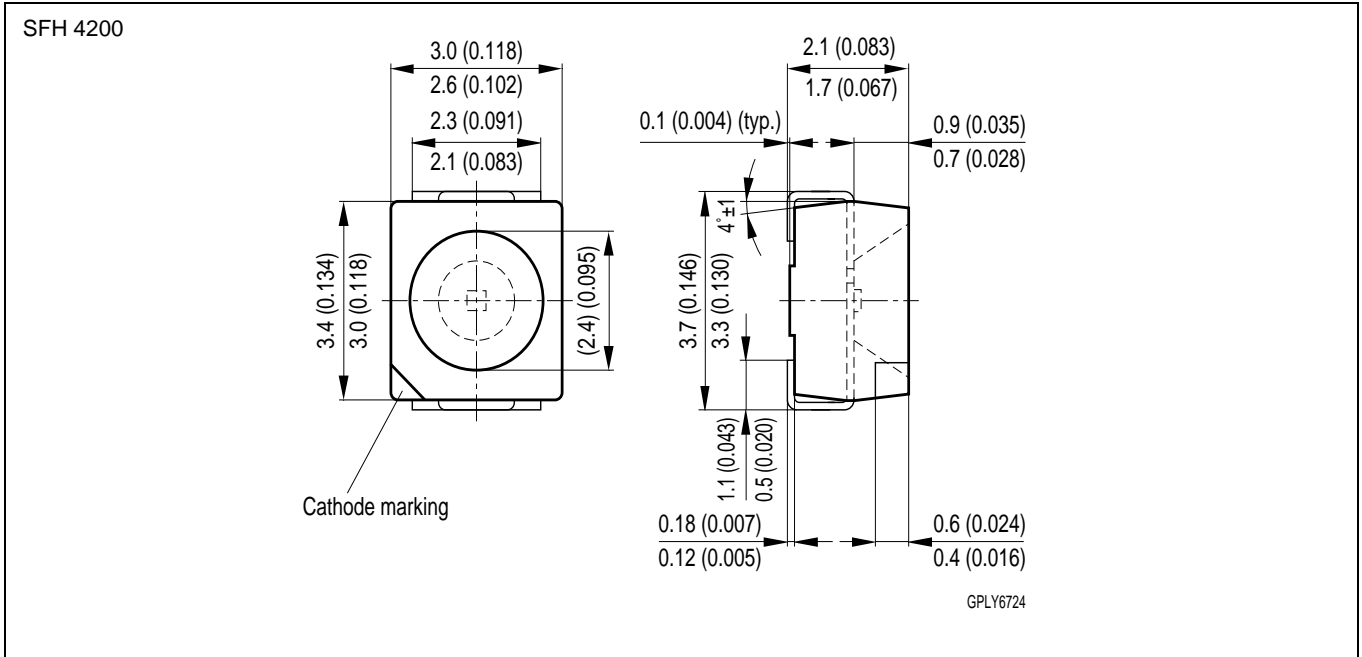
$I_F = f(\tau, T_A = 25\ \text{°C}, D = \text{parameter})$



Radiation Characteristics $I_{rel} = f(\varphi)$



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch)

Löthinweise Soldering Conditions

Bauform Types	Tauch-, Schwall- und Schlepplötlung Dip, Wave and Drag Soldering		Reflowlötlung Reflow Soldering	
	Lötbadtemperatur Temperature of the Soldering Bath	Maximal zulässige Lötzeit Max. Perm. Soldering Time	Lötzonen- temperatur Temperature of Soldering Zone	Maximale Durchlaufzeit Max. Transit Time
TOPLED	260 °C	10 s	245 °C	10 s
SIDELED	–	–	245 °C	10 s

Zusätzliche Informationen über allgemeine Lötbedingungen erhalten Sie auf Anfrage.

For additional information on general soldering conditions please contact us.

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Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components ¹, may only be used in life-support devices or systems ² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.